## NSN 5962-01-011-5625



Memory Microcircuit - Page 1 of 2 View Online at https://aerobasegroup.com/nsn/5962-01-011-5625 **Body Length:** 0.896 inches **Body Width:** Between 0.220 inches and 0.310 inches **Body Height:** Between 0.140 inches and 0.185 inches **Maximum Power Dissipation Rating:** 525.0 milliwatts **Operating Tempurature Range:** +0.0/+70.0 degrees celsius Storage Tempurature Range: -65.0/+150.0 degrees celsius **Features Provided:** Hermetically sealed and monolithic and positive outputs and w/enable and programmable and programmed and high speed and w/open **Inclosure Material:** Ceramic and glass **Inclosure Configuration:** Dual-in-line **Output Logic Form:** Transistor-transistor logic **Input Circuit Pattern:** 10 input **Case Outline Source And Designator:** D-2 mil-m-38510 **Terminal Surface Treatment:** Solder **Voltage Rating And Type Per Characteristic:** 5.5 volts power source **Time Rating Per Chacteristic:** 80.00 nanoseconds propagation delay time, low to high level output **Memory Device Type:** Rom **Test Data Document:** 28480-a-1816-9002-1 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Terminal Type And Quantity:** 16 printed circuit Shelf Life: N/a **Unit Of Measure:** 

Yes - demil/mli

**Demilitarization:** 

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